



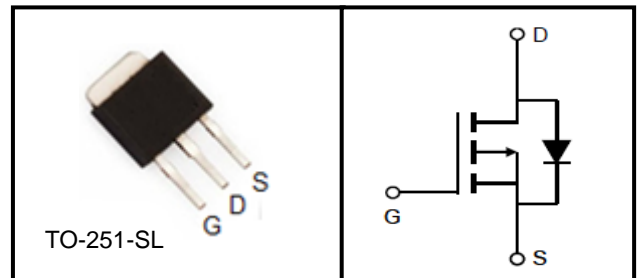
100V P-Channel Trench MOSFET

FEATURES

- Trench Power MOSFET Technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- Optimized For Fast-switching Applications

APPLICATIONS

- Load Switches
- Battery Switch



Device Marking and Package Information		
Device	Package	Marking
TTE01P10AT	TO-251-SL	01P10AT

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted			
Parameter	Symbol	Value	Unit
Drain-Source Voltage ($V_{GS} = 0\text{V}$)	V_{DSS}	-100	V
Continuous Drain Current	I_D	-1.5	A
Pulsed Drain Current (note1)	I_{DM}	-6	A
Gate-Source Voltage	V_{GSS}	± 20	V
Single Pulse Avalanche Energy (note2)	E_{AS}	0.8	mJ
Avalanche Current (note1)	I_{AR}	-2	A
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	1.5	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+175	$^\circ\text{C}$

Thermal Resistance			
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	20	K/W
Thermal Resistance, Junction-to-Ambient	R_{thJA}	60	



Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-100	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -100V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	-1	μA
		$V_{DS} = -100V, V_{GS} = 0V, T_J = 150^\circ\text{C}$	--	--	-100	
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20V$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1.0	--	-3.0	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -1A$	--	1.29	1.54	Ω
		$V_{GS} = -4.5V, I_D = -1A$	--	1.43	1.66	Ω
Forward Transconductance (Note3)	g_{fs}	$V_{DS} = -3V, I_D = -1.5A$		0.3	--	S
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0V,$ $V_{DS} = -25V,$ $f = 1.0\text{MHz}$	--	210	--	μF
Output Capacitance	C_{oss}		--	17	--	
Reverse Transfer Capacitance	C_{rss}		--	5	--	
Total Gate Charge	Q_g	$V_{DD} = -80V, I_D = -1A,$ $V_{GS} = -10V$	--	25	--	nC
Gate-Source Charge	Q_{gs}		--	3	--	
Gate-Drain Charge	Q_{gd}		--	7	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = -100V, I_D = -1A,$ $R_G = 2.5\Omega$	--	8	--	ns
Turn-on Rise Time	t_r		--	4	--	
Turn-off Delay Time	$t_{d(off)}$		--	32	--	
Turn-off Fall Time	t_f		--	7	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	$T_C = 25^\circ\text{C}$	--	--	-1	A
Pulsed Diode Forward Current	I_{SM}		--	--	-4	
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}, I_{SD} = -1A, V_{GS} = 0V$	--	--	-1.2	V
Reverse Recovery Time	t_{rr}	$I_F = -1A,$ $di_F/dt = 100A/\mu s$	--	25	--	ns
Reverse Recovery Charge	Q_{rr}		--	31	--	nC

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $I_{AS} = -2A, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse width $\leq 300\mu s$, Duty Cycle $\leq 1\%$



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

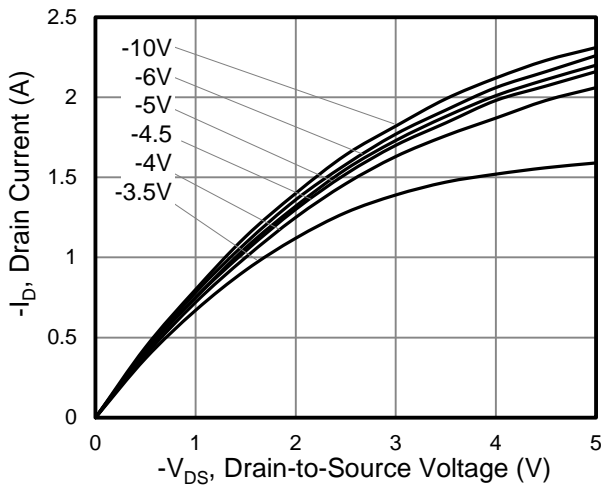


Figure 2. Transfer Characteristics

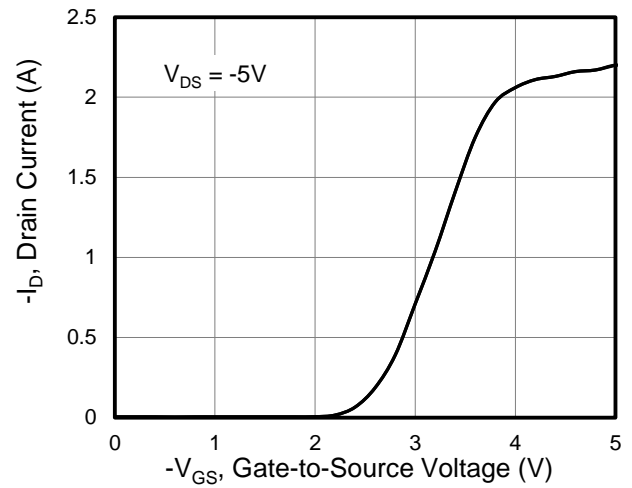


Figure 3. On-Resistance vs. Drain Current

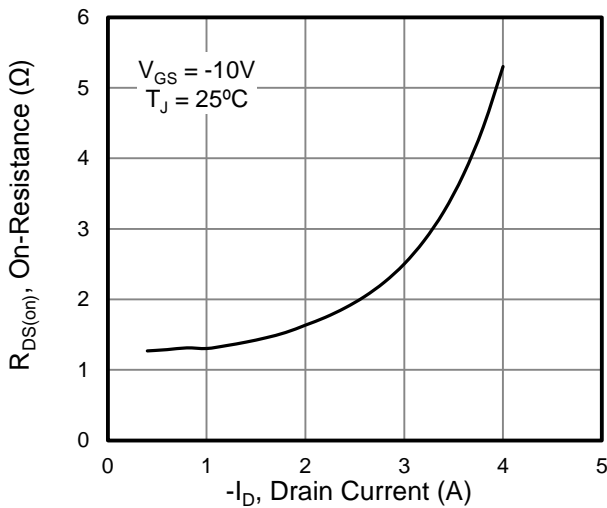


Figure 4. Capacitance

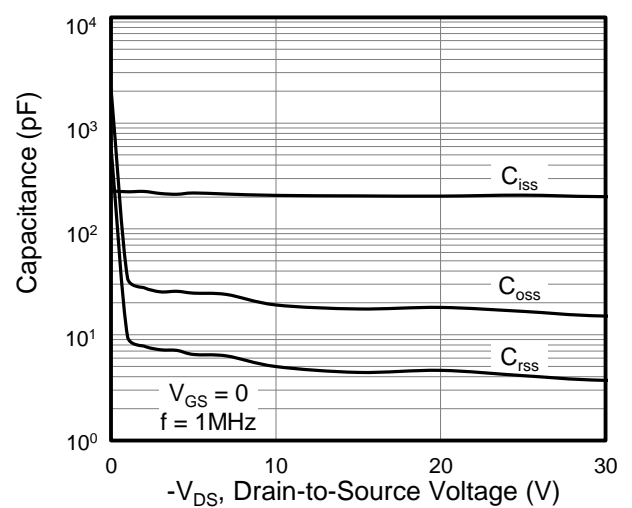


Figure 5. Gate Charge

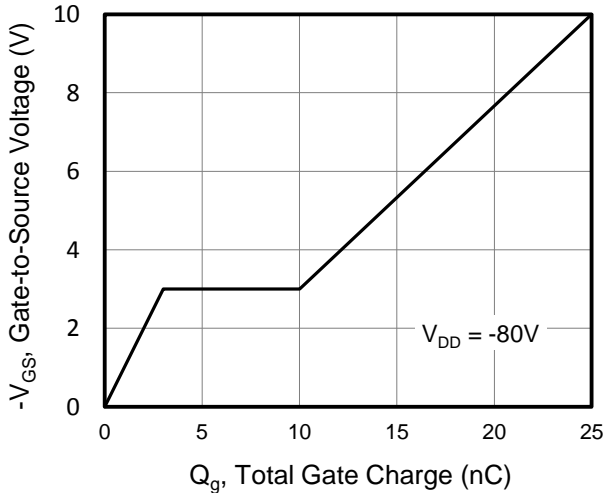
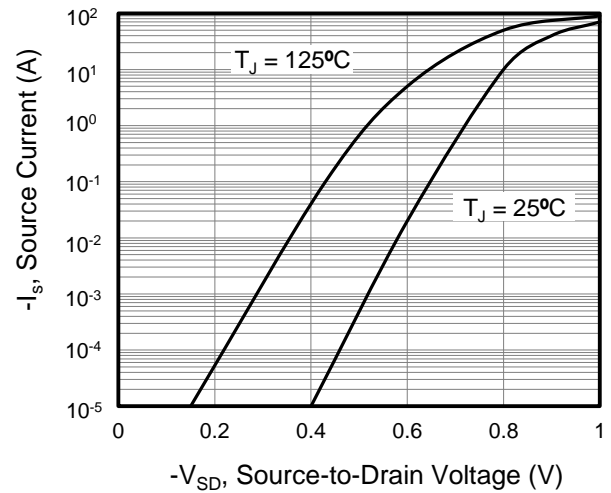


Figure 6. Body Diode Forward Voltage





Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. On-Resistance vs. Junction Temperature

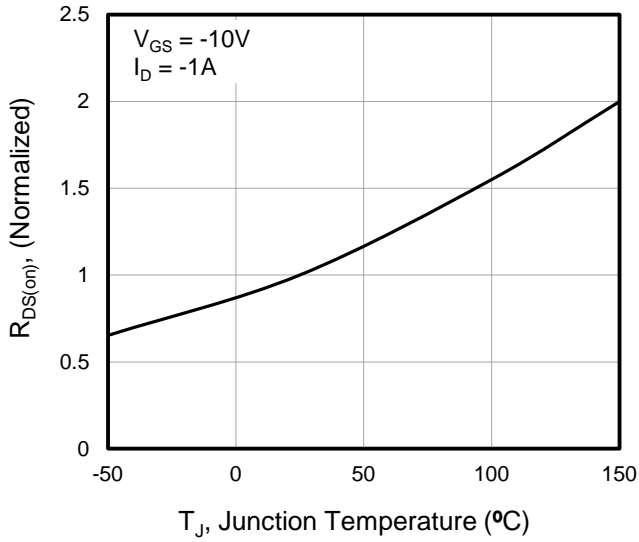


Figure 8. Threshold Voltage vs. Junction Temperature

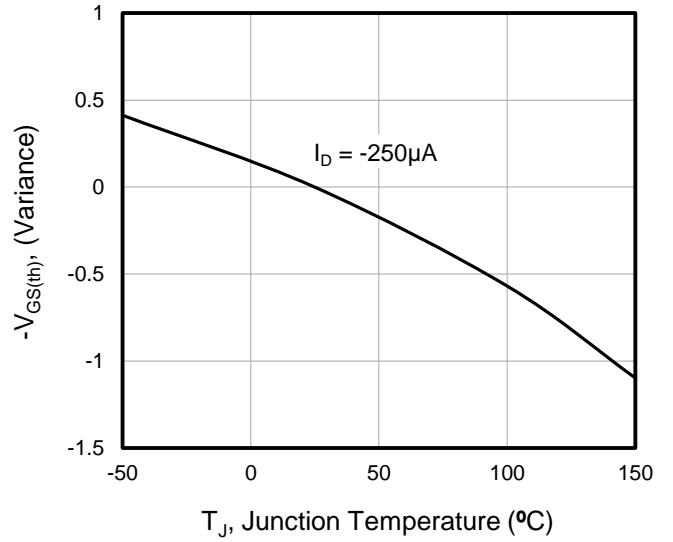


Figure 9. Transient Thermal Impedance

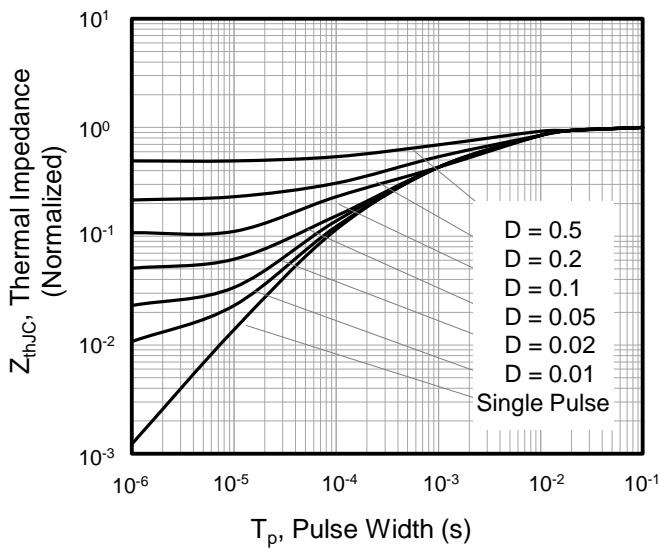




Figure A: Gate Charge Test Circuit and Waveform

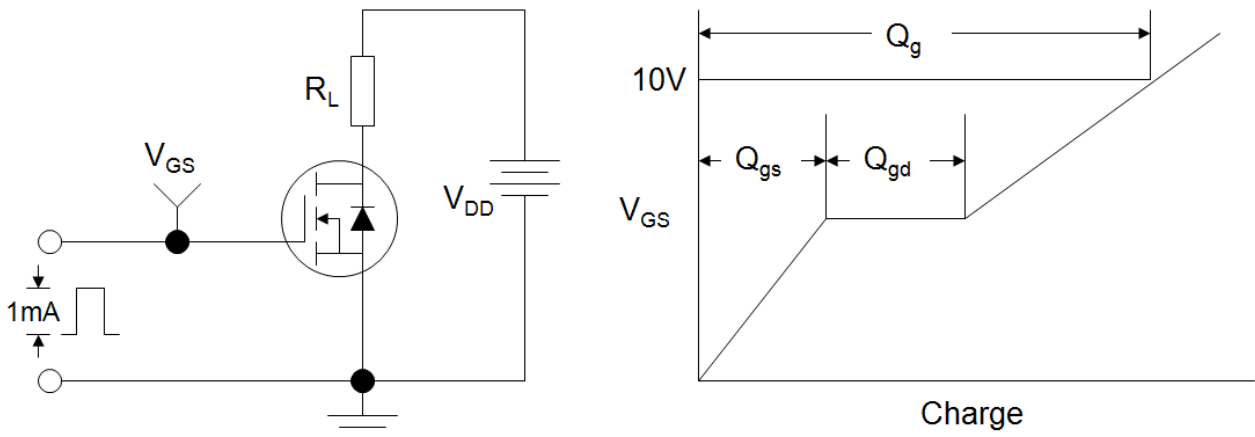
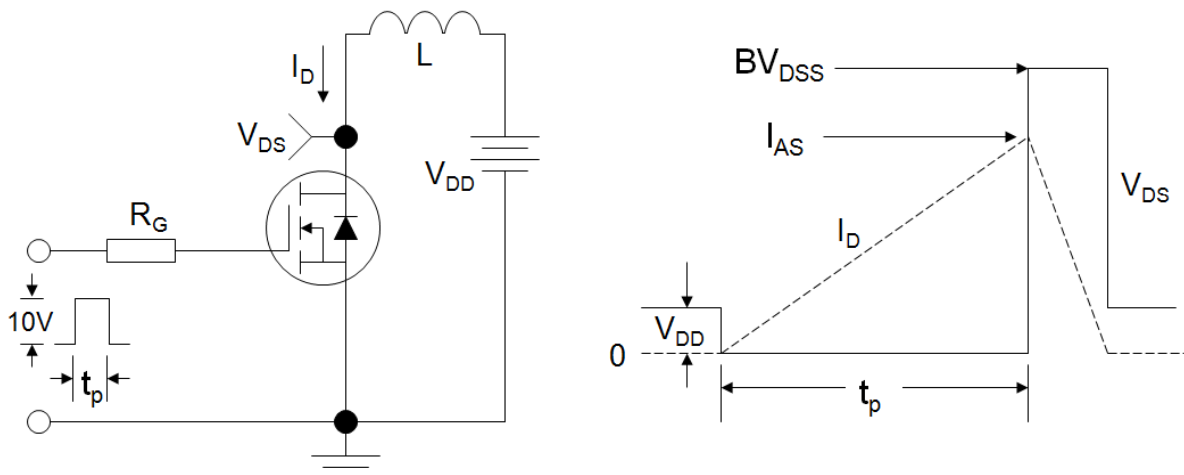


Figure B: Resistive Switching Test Circuit and Waveform

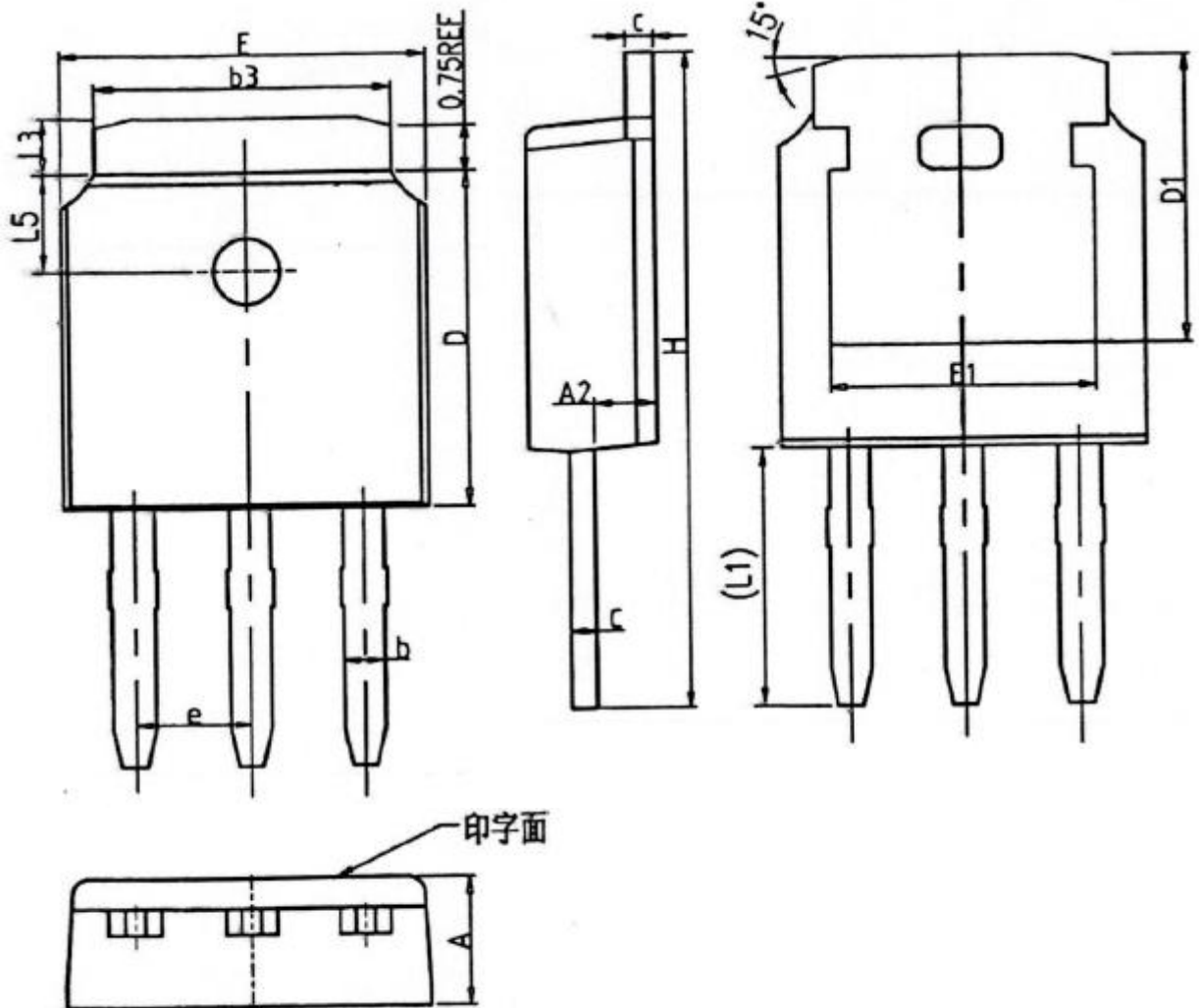


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





TO-251-SL



Unit: mm		
Symbol	Min.	Max.
A	2.20	2.40
A2	0.97	1.17
b	0.68	0.90
b2	0.00	0.10
b2'	0.00	0.10
b3	5.20	5.50
c	0.43	0.63
D	5.98	6.22

Unit: mm		
Symbol	Min.	Max.
D1	5.30REF	
E	6.40	6.80
E1	4.63	-
e	2.286BSC	
H	16.22	16.82
L1	9.15	9.65
L3	0.88	1.28
L5	1.65	1.95



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